



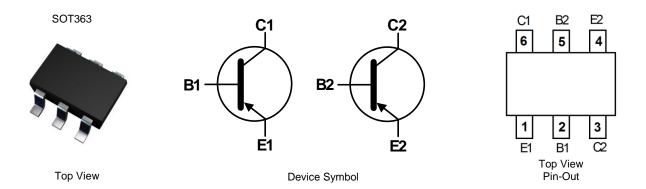
### 150V DUAL PNP SMALL SIGNAL TRANSISTOR IN SOT363

#### **Features**

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMDT5551)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (MMDT5401Q)

### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)



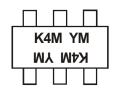
### **Ordering Information** (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT5401-7-F	K4M	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



K4M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2017	20	18	2019	2020	20	21	2022	2023	20	24	2025
Code	E	F	=	G	Н		I	J	K	l	-	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	Ic	-200	mA

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Dower Dissipation	(Note 5)	D	200	mW	
Power Dissipation	(Notes 6 & 7)	P <sub>D</sub>	320		
Thermal Desistance Junction to Ambient	(Note 5)	D	625		
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{ hetaJA}$	390	°C/W	
Thermal Resistance, Junction to Case (Note 8)		R <sub>θJC</sub>	140		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-160			V	$I_C = -100\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-150			V	$I_C = -1 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6			٧	$I_E = -100\mu A, I_C = 0$		
Collector-Base Cutoff Current			_	-50	nA	$V_{CB} = -120V, I_E = 0$		
Collector-Base Cuton Current	I <sub>CBO</sub>	_		-50	μΑ	$V_{CB} = -120V$ , $I_E = 0$ , $T_A = +100$ °C		
Base-Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-50	nA	$V_{EB} = -5V, I_C = 0$		
ON CHARACTERISTICS (Note 9)	ON CHARACTERISTICS (Note 9)							
		50			_	$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$		
DC Current Gain	h <sub>FE</sub>	60	_	240		$I_C = -10 \text{mA}, V_{CE} = -5.0 \text{V}$		
		50				$I_C = -50 \text{mA}, V_{CE} = -5.0 \text{V}$		
Collector Emitter Seturation Voltage	.,		_	-0.2	V	$I_C = -10mA$ , $I_B = -1.0mA$		
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_		-0.5		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$		
Base Emitter Ceturation Voltage	V <sub>BE(SAT)</sub>		_	-1.0	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA		
Base-Emitter Saturation Voltage		_				$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$		
SMALL SIGNAL CHARACTERISTICS								
Output Capacitance	$C_{obo}$	_		6.0	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$		
Small Signal Current Gain	h <sub>fe</sub>	40		260	_	$I_C = -1mA$ , $V_{CE} = -10V$ , $f = 1.0MHz$		
Current Gain-Bandwidth Product	f⊤	100	_	300	MHz	$I_C = -10$ mA, $V_{CE} = -10$ V, $f = 100$ MHz		
Noise Figure	NF	_	_	8.0	dB	$\begin{split} V_{CE} = -5.0V, \ I_C = -200\mu A, \\ R_S = 10\Omega, f = 1.0kHz \end{split}$		

Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted 25mm X 25mm 2oz copper.
- 7. Maximum combined dissipation.
- 8. Thermal resistance from junction to the top of package.
- 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

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## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

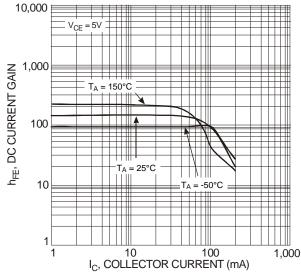
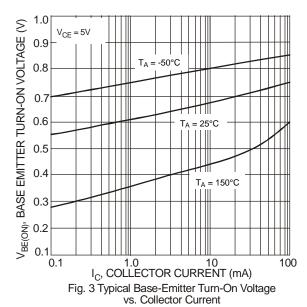


Fig. 1 Typical DC Current Gain vs. Collector Current



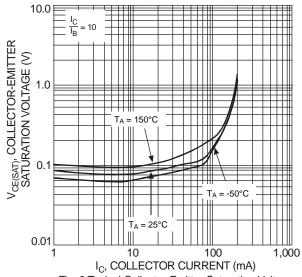


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

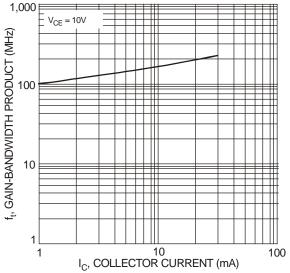


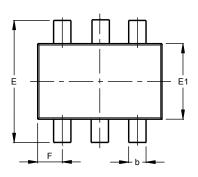
Fig. 4 Typical Gain-Bandwidth Product vs Collector Current

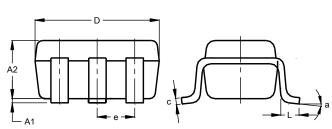


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



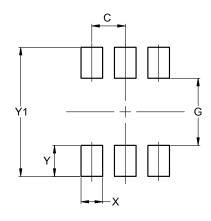


SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
E	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



Dimensions	Value		
Dilliensions	(in mm)		
С	0.650		
G	1.300		
Х	0.420		
Y	0.600		
Y1	2.500		

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For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking. Note:

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